MOSFETs Silicon N-Channel MOS (DTMOSVI)

# TK110A65Z

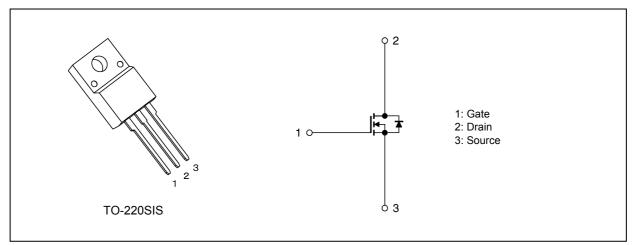
#### 1. Applications

• Switching Power Supplies

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.092 \Omega$  (typ.)
- (2) High-speed switching properties with the lower capacitance.
- (3) Enhancement mode:  $V_{th}$  = 3 to 4 V ( $V_{DS}$  = 10 V,  $I_D$  = 1.02 mA)

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics			Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	650	V
Gate-source voltage	·	V <sub>GSS</sub>	±30	1
Drain current (DC)	(Note 1)	I <sub>D</sub>	24	A
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	96	1
Power dissipation (T <sub>c</sub>	= 25 °C)	PD	45	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	258	mJ
Single-pulse avalanche current		I <sub>AS</sub>	6	Α
Reverse drain current (DC)	(Note 1)	I <sub>DR</sub>	24	1
Reverse drain current (pulsed)	(Note 1)	I <sub>DRP</sub>	96	1
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	1
Isolation voltage (RMS)		V <sub>ISO(RMS)</sub>	2000	V
Mounting torque		TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2020-02

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	2.77	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	62.5	

Note 1: Ensure that the channel temperature does not exceed 150 °C. Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25 °C (initial), L = 12.7 mH,  $I_{AS}$  = 6 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25 $^{\circ}$ C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±30 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current	I <sub>DSS</sub>	$V_{DS}$ = 650 V, $V_{GS}$ = 0 V	_	_	2	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	650	—	—	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.02 mA	3	—	4	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A		0.092	0.11	Ω

### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	$V_{DS}$ = 300 V, $V_{GS}$ = 0 V, f = 100 kHz		2250	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	]		1.9	_	
Output capacitance	C <sub>oss</sub>			54		
Effective output capacitance	C <sub>o(er)</sub>	$V_{DS}$ = 0 to 400 V, $V_{GS}$ = 0 V	_	85	_	pF
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN , f = 1 MHz		3.4	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1		28	_	ns
Switching time (turn-on time)	t <sub>on</sub>	1		52		
Switching time (fall time)	t <sub>f</sub>	1		4	_	
Switching time (turn-off time)	t <sub>off</sub>	]		90		ns
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} \le V_{(BR)DSS}, I_D \le 12 \text{ A}$	90	_	_	V/ns

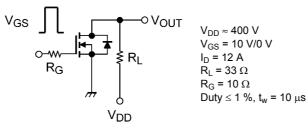


Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400$ V, $V_{GS}$ = 10 V, $I_D$ = 24 A	—	40	—	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	13	_	
Gate-drain charge	Q <sub>gd</sub>		_	11	—	

## 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 24 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	V <sub>DD</sub> = 400 V,	_	300	_	ns
Reverse recovery charge	Q <sub>rr</sub>	I <sub>DR</sub> = 12 A, V <sub>GS</sub> = 0 V -dI <sub>DR</sub> /dt = 100 A/μs	_	3.9	_	μC
Peak reverse recovery current	l <sub>rr</sub>		_	26	—	A
Diode dv/dt ruggedness	dv/dt	$V_{DD} \leq 400$ V, $I_{DR} \leq 12$ A, $V_{GS}$ = 0 V	40	_	_	V/ns

### 7. Marking (Note)

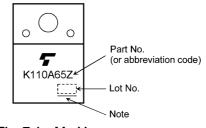
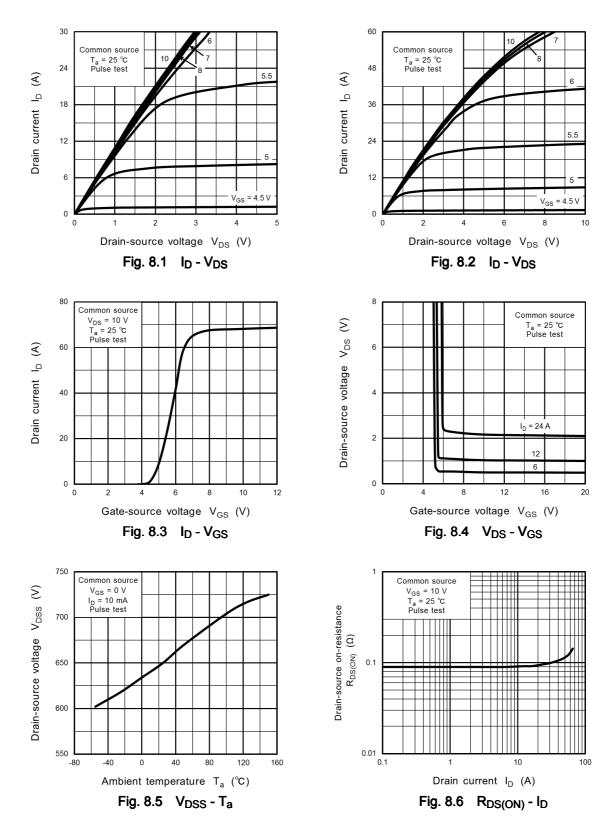
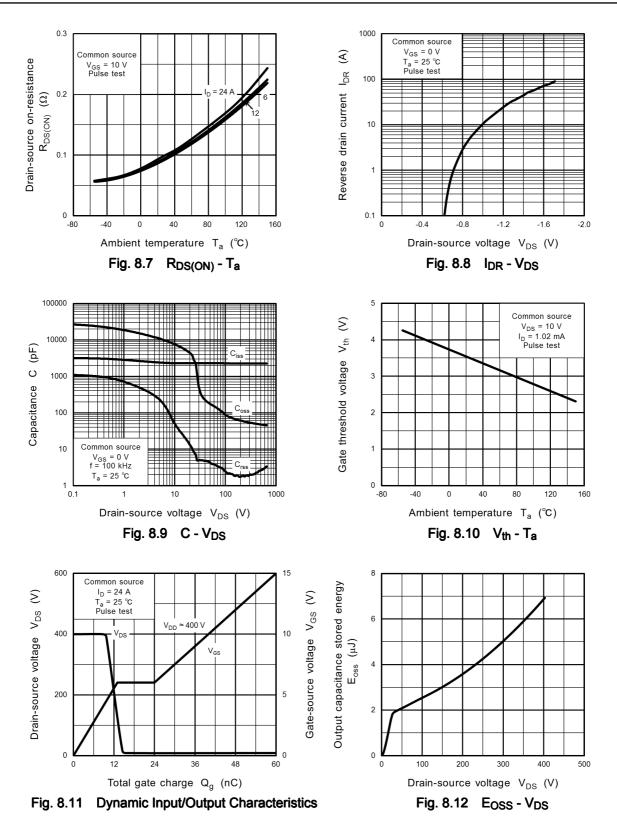


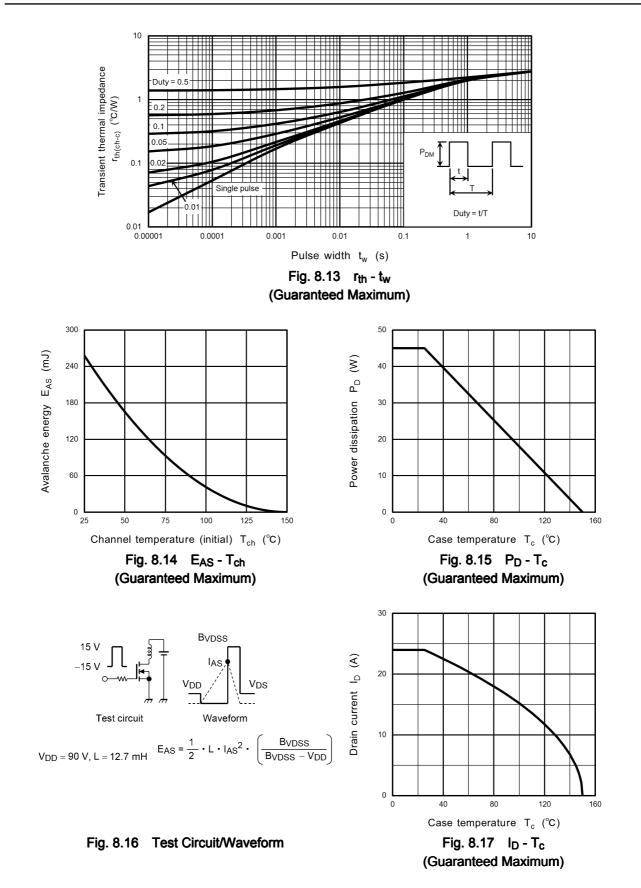
Fig. 7.1 Marking

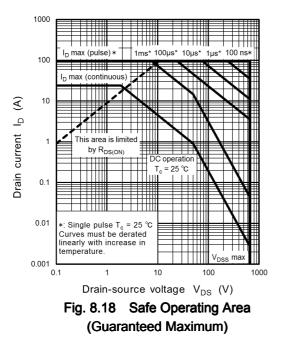
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### 8. Characteristics Curves (Note)







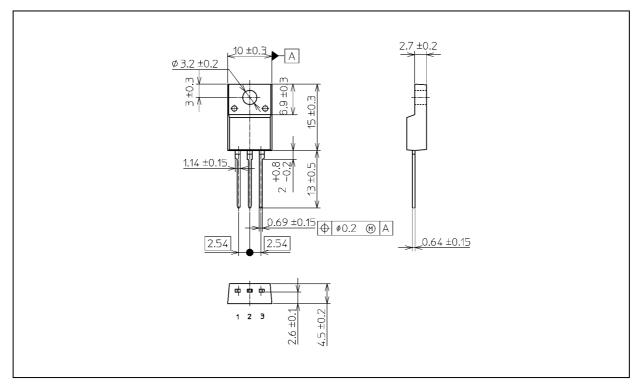


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## TK110A65Z

#### **Package Dimensions**

Unit: mm



#### Weight: 1.7 g (typ.)

Package Name(s)		
JEITA: SC-67		
TOSHIBA: 2-10U1S		
Nickname: TO-220SIS		

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